

Список основных публикаций официального оппонента

**Мохова Евгения Николаевича**

по тематике диссертации Лебедева С.П.

**«ПОЛУЧЕНИЕ ГРАФЕНА МЕТОДОМ ДИССОЦИАТИВНОГО  
ИСПАРЕНИЯ (СУБЛИМАЦИИ) ПОВЕРХНОСТИ SiC И  
ИССЛЕДОВАНИЕ СВОЙСТВ СТРУКТУР ГРАФЕН/SiC»**

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